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Yoksis Araştırmacı ID: [7536](https://yoksis.gazi.edu.tr/7536)

Eğitim Bilgileri

Doktora, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (Dr), Türkiye 1986 - 1994

Yüksek Lisans, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), Türkiye 1983 - 1985

Lisans, Fırat Üniversitesi, Fen Fakültesi, Fizik Bölümü, Türkiye 1978 - 1982

Yaptığı Tezler

Doktora, Al-siox-psi aygıtların ve güneş pillerinin elektriksel karakteristikleri, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (Dr), 1993

Yüksek Lisans, Çok ince yapı teorisi, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), 1950

Araştırma Alanları

Yarıiletken ve Süperiletken Malzemeler, Optik Özellikler, Kompozitler, Nanomalzemeler, Yoğun Madde 1:Yapısal, Mekanik ve Termal Özellikler, Yoğun Madde 2:Elektronik Yapı, Elektrik, Manyetik ve Optik Özellikler

Akademik Unvanlar / Görevler

Prof. Dr., Gazi Üniversitesi, Fen Fakültesi, Fizik, 2011 - Devam Ediyor

Doç. Dr., Gazi Üniversitesi, Fen Fakültesi, Fizik, 2005 - 2011

Yrd. Doç. Dr., Gazi Üniversitesi, Fen Fakültesi, Fizik, 1994 - 2005

Araştırma Görevlisi, Gazi Üniversitesi, Fen Fakültesi, Fizik, 1983 - 1994

Yönetilen Tezler

ALTINDAL Ş., Photovoltaic and temperature Characteristics of the designed Schottky barrier diodes (SBDs) as a function of temperature and illumination, Doktora, H.MELOUD(Öğrenci), 2021

ALTINDAL Ş., Au/(nanografite-PVP)/n-Si (MPS) yapılarının hazırlanması ve elektrik ile dielektrik özelliklerinin geniş bir frekans ve voltaj aralığında incelenmesi, Doktora, A.MUHAMMED(Öğrenci), 2021

Altındal Ş., Dielektrik çok katmanlı geniş bantlı kızılötesi metamalzeme soğurucunun tasarımı, üretimi ve karakterizasyonu, Doktora, B.AKIN(Öğrenci), 2021

ALTINDAL Ş., Au/(Ag-ZnO/PVP)/n-Si (MPS) Schottky engel diyotların hazırlanması ve elektrik ile dielektrik özelliklerinin frekans ve voltaja bağlı incelenmesi, Doktora, Ö.SEVGİLİ(Öğrenci), 2020

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ALTINDAL Ş., Grafen katkılı p-tipi ve n-tipi termoelektrik nanokompozit malzeme üretimi ve karakterizasyonu, Yüksek Lisans, S.KOÇYİĞİT(Öğrenci), 2017

ALTINDAL Ş., USLU İ., Grafen katkılı p-tipi ve n-tipi termoelektrik nanokompozit malzeme üretimi ve karakterizasyonu, Yüksek Lisans, S.KOÇYİĞİT(Öğrenci), 2017

ALTINDAL Ş., Polimer arayüzey tabakalı ve tabakasız schottky engel diyotların elektriksel karakteristiklerinin karşılaştırılması, Doktora, Ç.BİLKAN(Öğrenci), 2016

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ALTINDAL Ş., Au/n-GaAs Schottky diyotların hazırlanması ve akım-iletim mekanizmalarının geniş bir sıcaklık aralığında incelenmesi, Doktora, E.ÖZAVCI(Öğrenci), 2015

ALTINDAL Ş., Au/Ca₃Co₄Ga_{0,001}Ox/n-Si yapılarında doğru ve ters beslem akım-voltaj (I-V) karakteristiklerinin 80-340 K sıcaklık aralığında incelenmesi, Doktora, E.MARIL(Öğrenci), 2015

ALTINDAL Ş., Zirkonyum oksit ve gadolinyum oksit tabanlı çeşitli metal oksit katkılı inorganik pigmentlerin çöz-pel tekniğiyle sentezi ve karakterizasyonu, Yüksek Lisans, A.AYTİMUR(Öğrenci), 2015

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ALTINDAL Ş., Au/(%1 Grafen Katkılı)-Ca_{1.9}Pr_{0.1}Co₄Ox/N-Si Schottky Engel Diyotların Hazırlanması Ve Elektrik ile Dielektrik Özelliklerinin Sıcaklık Ve Frekansa Bağlı incelenmesi, Doktora, H.Gökçen(Öğrenci), 2015

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ALTINDAL Ş., Metal-polimer-yarıiletken (MPS) yapıların elektrik ve dielektrik özelliklerinin geniş frekans aralığında

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ALTINDAL Ş., (Ni/Au)/Al_{0.22}Ga_{0.78}N/AlN/GaN çoklu-yapıların elektriksel karakteristiklerinin admitans spektroskopisiyle incelenmesi, Doktora, Y.ŞAFAK(Öğrenci), 2012

ALTINDAL Ş., Au/PVA:Zn/n-Si (MPS)schottky engel diyodun elektriksel özelliklerinin sıcaklık ve radyasyona bağlı incelenmesi, Doktora, İ.TAŞÇIOĞLU(Öğrenci), 2012

ALTINDAL Ş., Metal-yalıtkan-yarıiletken (Al/SiO₂/p-Si) yapıların elektrik ve dielektrik özelliklerinin frekans ve potansiyele bağlı incelenmesi, Doktora, Z.SÖNMEZ(Öğrenci), 2012

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ALTINDAL Ş., Al / Rhodamine - 101 / n-GaAs Schottky Engel diyotlarının hazırlanması ve iletim mekanizmalarının geniş bir sıcaklık aralığında incelenmesi, Doktora, Ö.VURAL(Öğrenci), 2011

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ALTINDAL Ş., Al/SiO₂/p-Si (MIS) yapıların elektrik karakteristiklerinin frekansa bağlı incelenmesi, Yüksek Lisans, A.KAYA(Öğrenci), 2010

ALTINDAL Ş., Al/SiO₂/p-Si (MIS) yapıların elektrik karakteristiklerinin frekansa bağlı incelenmesi, Yüksek Lisans, A.KAYA(Öğrenci), 2010

ALTINDAL Ş., Au/(Co, Zn-katkılı) polivinil alkol/n-Si schottky engel diyotlarının hazırlanması ve elektriksel özelliklerinin aydınlatma şiddetine bağlı incelenmesi, Doktora, H.USLU(Öğrenci), 2010

ALTINDAL Ş., NiAu-AlGa_{0.4}N/GaN heteroyapıların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Doktora, S.DEMİREZEN(Öğrenci), 2010

ALTINDAL Ş., NiAu-AlGa_{0.4}N/GaN heteroyapıların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Doktora, S.DEMİREZEN(Öğrenci), 2010

ALTINDAL Ş., SiO₂/p-Si (MIS) YAPILARIN ELEKTRİK KARAKTERİSTİKLERİNİN FREKANS BAĞLI İNCELENMESİ, Yüksek Lisans, A.KAYA(Öğrenci), 2010

ALTINDAL Ş., NiAu-AlGa_{0.4}N/GaN HETEROYAPILARIN ELEKTRİKSEL KARAKTERİSTİKLERİNİN SICAKLIĞA BAĞLI İNCELENMESİ, Doktora, S.DEMİREZEN(Öğrenci), 2010

ALTINDAL Ş., Au/(Co, Zn-katkılı) polivinil alkol/n-Si schottky engel diyotlarının hazırlanması ve elektriksel özelliklerinin aydınlatma şiddetine bağlı incelenmesi, Doktora, H.USLU(Öğrenci), 2010

ALTINDAL Ş., Au/SrTiO₃/n-Si (MFS) Schottky diyotların elektriksel parametrelerinin I-V, C-V ve DLTS metodu ile incelenmesi, Yüksek Lisans, U.AYDEMİR(Öğrenci), 2009

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ALTINDAL Ş., Yalıtkan tabakalı Al/p-Si Schottky diyotlarda elektriksel karakteristiklerin sıcaklığa bağlı incelenmesi, Doktora, H.KANBUR(Öğrenci), 2008

ALTINDAL Ş., Au/SiO₂/n-GaAs (MOY) YAPILARIN ELEKTRİK VE DİELEKTRİK KARAKTERİSTİKLERİNİN FREKANS VE SICAKLIĞA BAĞLI İNCELENMESİ, Doktora, M.GÖKÇEN(Öğrenci), 2008

ALTINDAL Ş., Al/ SiO₂/p-Si (MYI) YAPILARIN AKIM-İLETİM MEKANİZMASI VE ELEKTRİKSEL ÖZELLİKLERİNİN SICAKLIĞA BAĞLI İNCELENMESİ, Doktora, D.Esra(Öğrenci), 2008

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ALTINDAL Ş., MIS yapıların frekans ve radyasyona bağlı temel elektriksel parametreleri, Yüksek Lisans, B.TATAROĞLU(Öğrenci), 2006

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ALTINDAL Ş., MOS yapılarda temel fiziksel parametrelerin frekans ve radyasyon miktarına bağlı incelenmesi, Doktora, A.TATAROĞLU(Öğrenci), 2004

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ALTINDAL Ş., Yalıtkan arayüzey tabakası ve seri dirence sahip Al/ SnO₂/ p-Si schottky diyotların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Yüksek Lisans, Z.TEKELİ(Öğrenci), 2002

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barrier diodes (SBDs) at room temperature

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